

DATA SHEET

PDTA144E series

PNP resistor-equipped transistors;

$R1 = 47\text{ k}\Omega$, $R2 = 47\text{ k}\Omega$

Product specification
Supersedes data of 2003 Apr 10

2004 Aug 05

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PDTA144E series

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	–	–50	V
I _O	output current (DC)	–	–100	mA
R1	bias resistor	47	–	k Ω
R2	bias resistor	47	–	k Ω

DESCRIPTION

PNP resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	NPN COMPLEMENT
	PHILIPS	EIAJ		
PDTA144EE	SOT416	SC-75	07	PDTC144EE
PDTA144EEF	SOT490	SC-89	07	PDTC144EEF
PDTA144EK	SOT346	SC-59	07	PDTC144EK
PDTA144EM	SOT883	SC-101	DR	PDTC144EM
PDTA144ES	SOT54 (TO-92)	SC-43	TA144E	PDTC144ES
PDTA144ET	SOT23	–	*07 ⁽¹⁾	PDTC144ET
PDTA144EU	SOT323	SC-70	*07 ⁽¹⁾	PDTC144EU

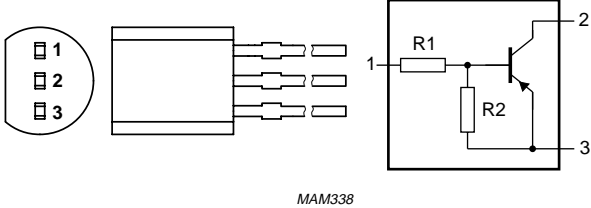
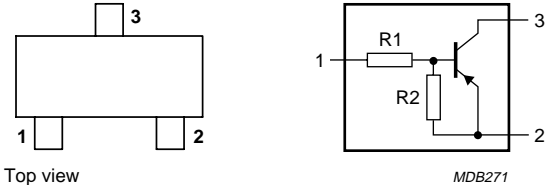
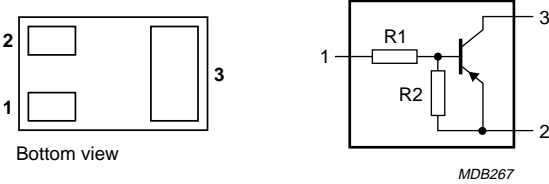
Note

- * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

PNP resistor-equipped transistors;
R1 = 47 kΩ, R2 = 47 kΩ

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SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTA144ES	 MAM338	1 2 3	base collector emitter
PDTA144EE PDTA144EEF PDTA144EK PDTA144ET PDTA144EU	 Top view MDB271	1 2 3	base emitter collector
PDTA144EM	 Bottom view MDB267	1 2 3	base emitter collector

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	–50	V
V _{CEO}	collector-emitter voltage	open base	–	–50	V
V _{EBO}	emitter-base voltage	open collector	–	–10	V
V _I	input voltage				
	positive		–	+10	V
	negative		–	–40	V
I _O	output current (DC)		–	–100	mA
I _{CM}	peak collector current		–	–100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT416	note 1	–	150	mW
	SOT490	notes 1 and 2	–	250	mW
	SOT883	notes 2 and 3	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

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2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

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CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = -50 V; I _E = 0	–	–	-100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = -30 V; I _B = 0	–	–	-1	μ A
		V _{CE} = -30 V; I _B = 0; T _j = 150 °C	–	–	-50	μ A
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0	–	–	-90	μ A
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -5 mA	80	–	–	
V _{CEsat}	collector-emitter saturation voltage	I _C = -10 mA; I _B = -0.5 mA	–	–	-150	mV
V _{i(off)}	input-off voltage	I _C = -100 μ A; V _{CE} = -5 V	–	-1.2	-0.8	V
V _{i(on)}	input-on voltage	I _C = -2 mA; V _{CE} = -0.3 V	-3	-1.6	–	V
R1	input resistor		33	47	61	k Ω
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = -10 V; f = 1 MHz	–	–	3	pF

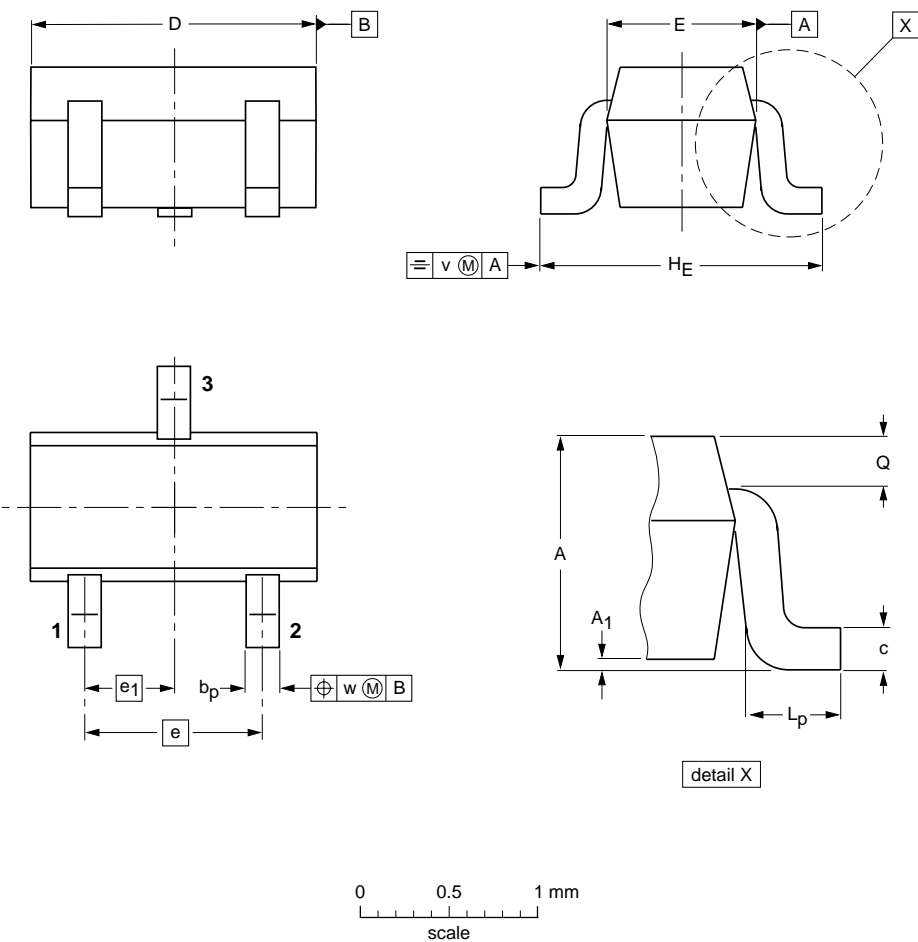
PNP resistor-equipped transistors;
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PACKAGE OUTLINES


Plastic surface mounted package; 3 leads

SOT416



DIMENSIONS (mm are the original dimensions)

UNIT	A	A1 max	bp	c	D	E	e	e1	HE	Lp	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

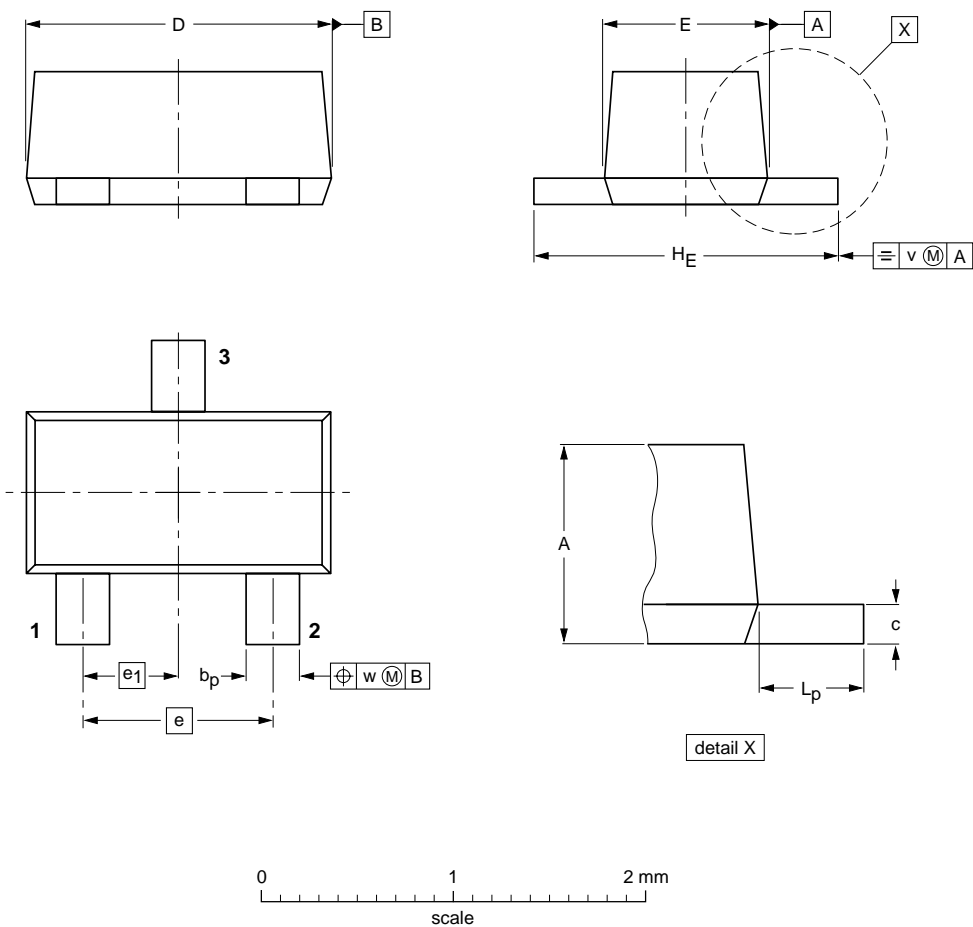
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	IEC	JEDEC	EIAJ			
SOT416			SC-75			97-02-28

PNP resistor-equipped transistors;
R1 = 47 kΩ, R2 = 47 kΩ

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Plastic surface mounted package; 3 leads

SOT490



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	e	e ₁	H _E	L _p	v	w
mm	0.8 0.6	0.33 0.23	0.2 0.1	1.7 1.5	0.95 0.75	1.0	0.5	1.7 1.5	0.5 0.3	0.1	0.1

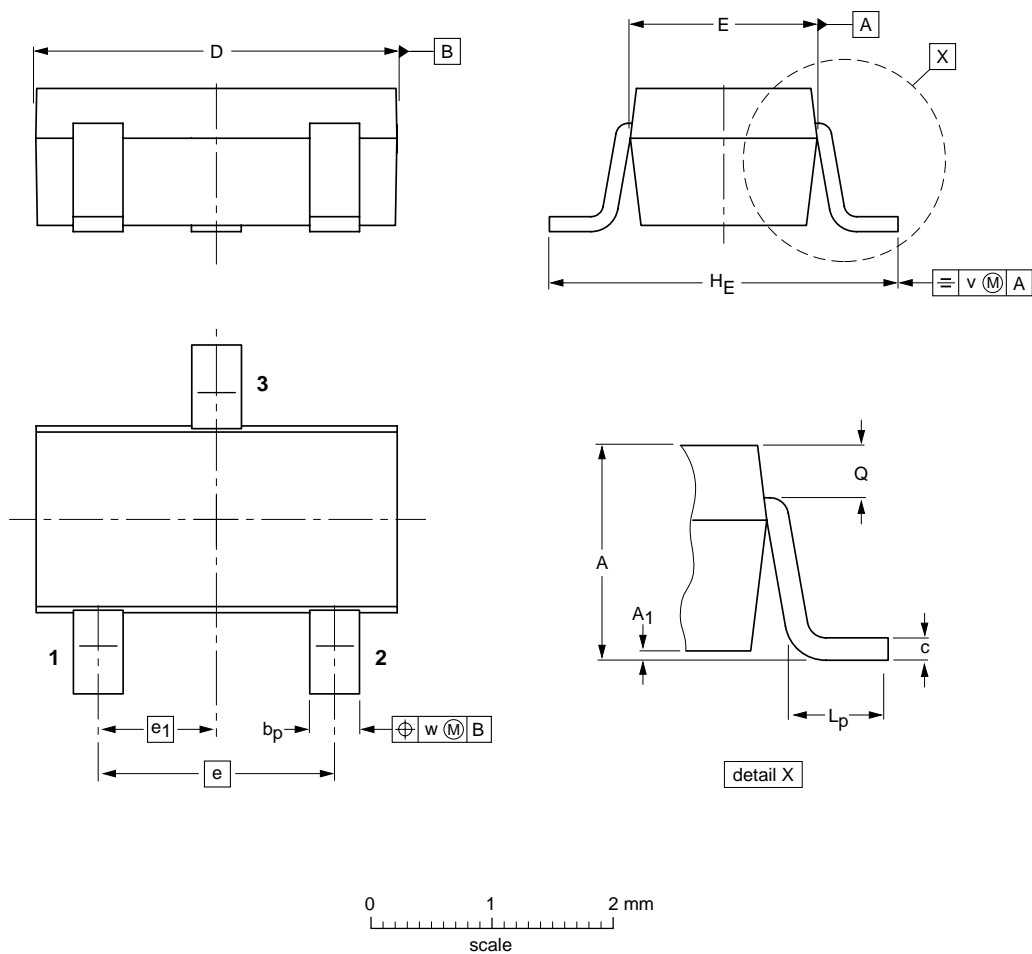
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	IEC	JEDEC	EIAJ			
SOT490			SC-89			98-10-23

PNP resistor-equipped transistors;
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

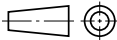
Plastic surface mounted package; 3 leads

SOT346



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

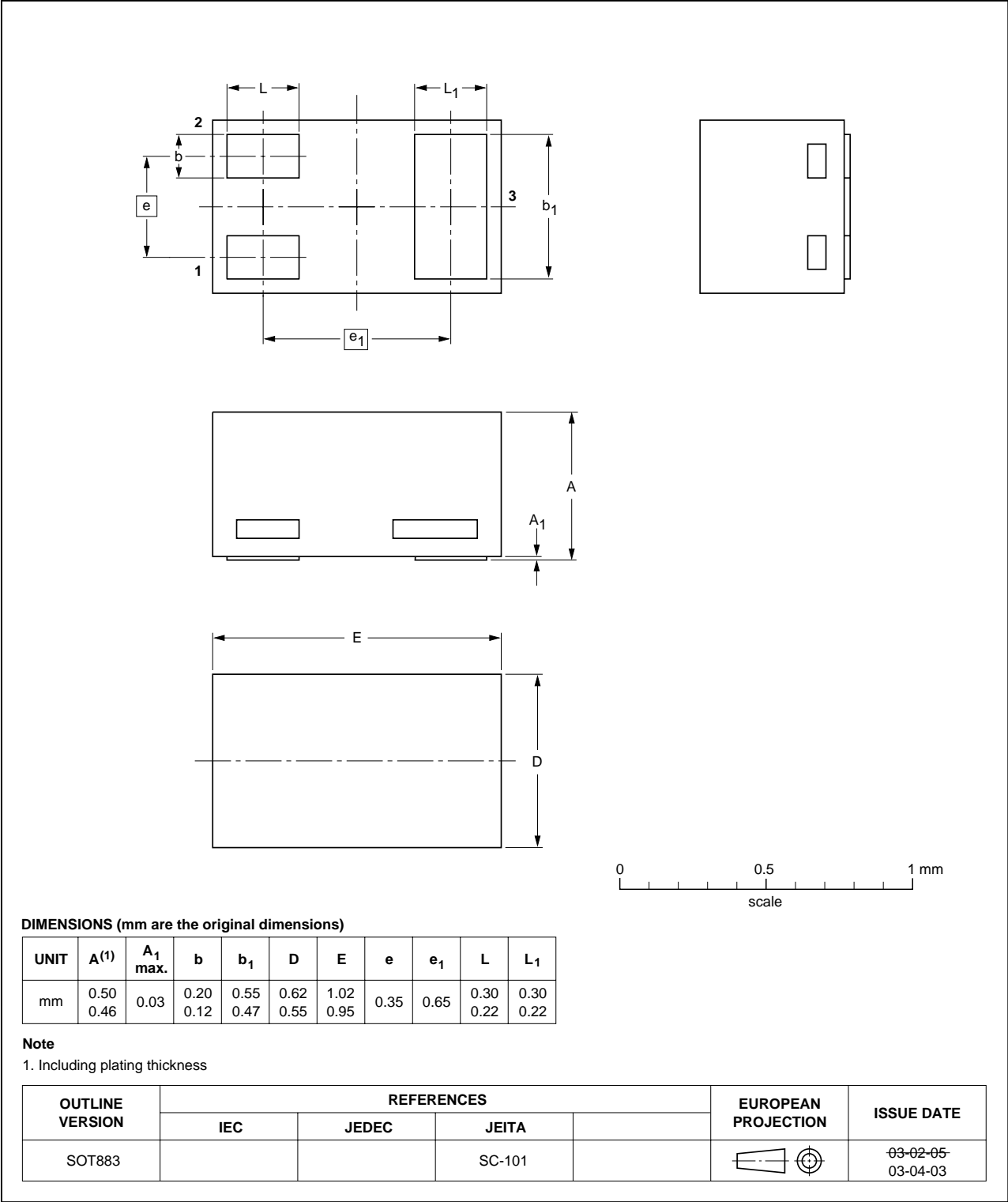
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT346		TO-236	SC-59			98-07-17

PNP resistor-equipped transistors;
R1 = 47 kΩ, R2 = 47 kΩ

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Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883

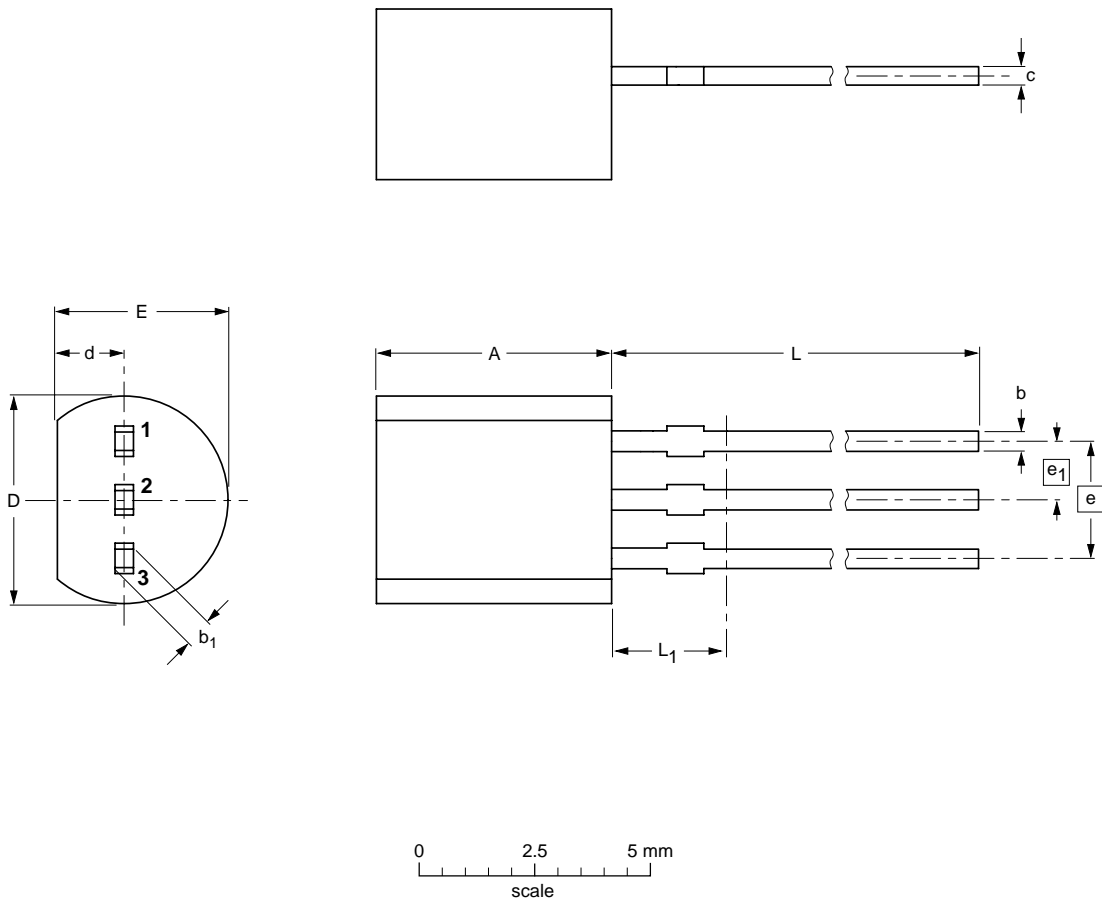


PNP resistor-equipped transistors;
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

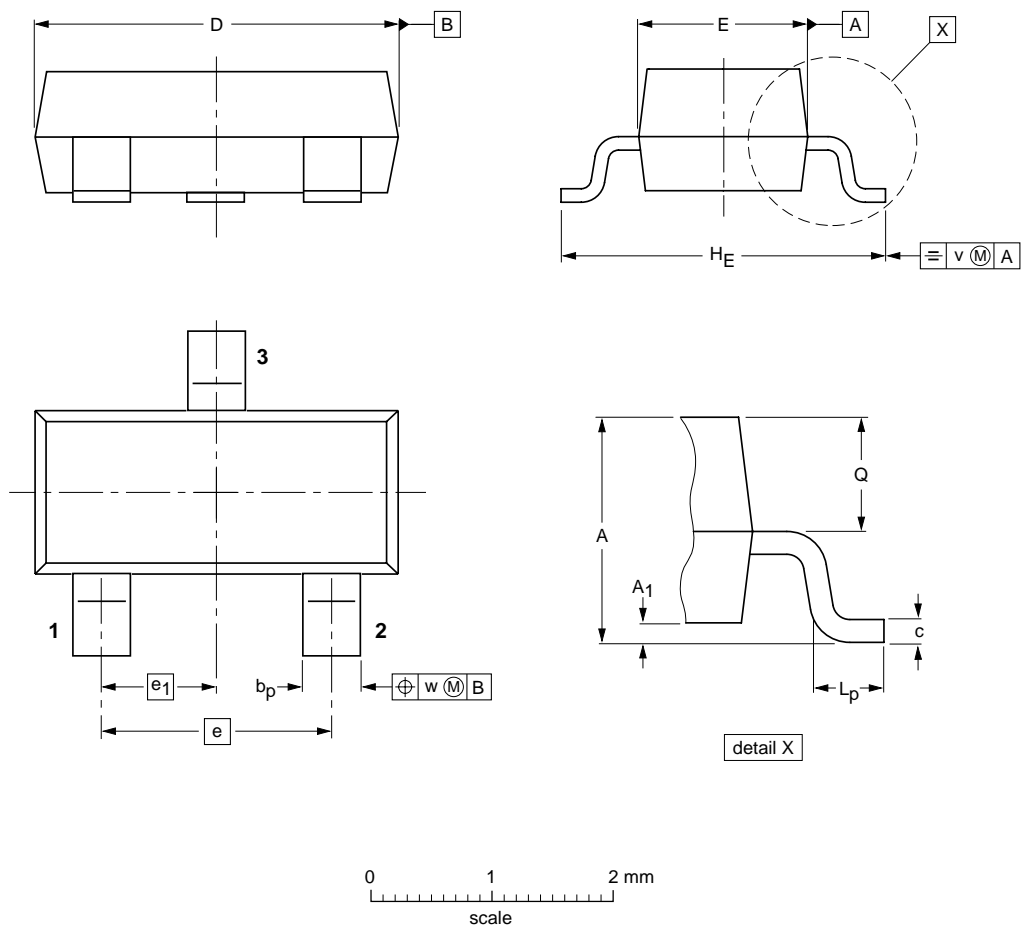
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			97-02-28 04-06-28

PNP resistor-equipped transistors;
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

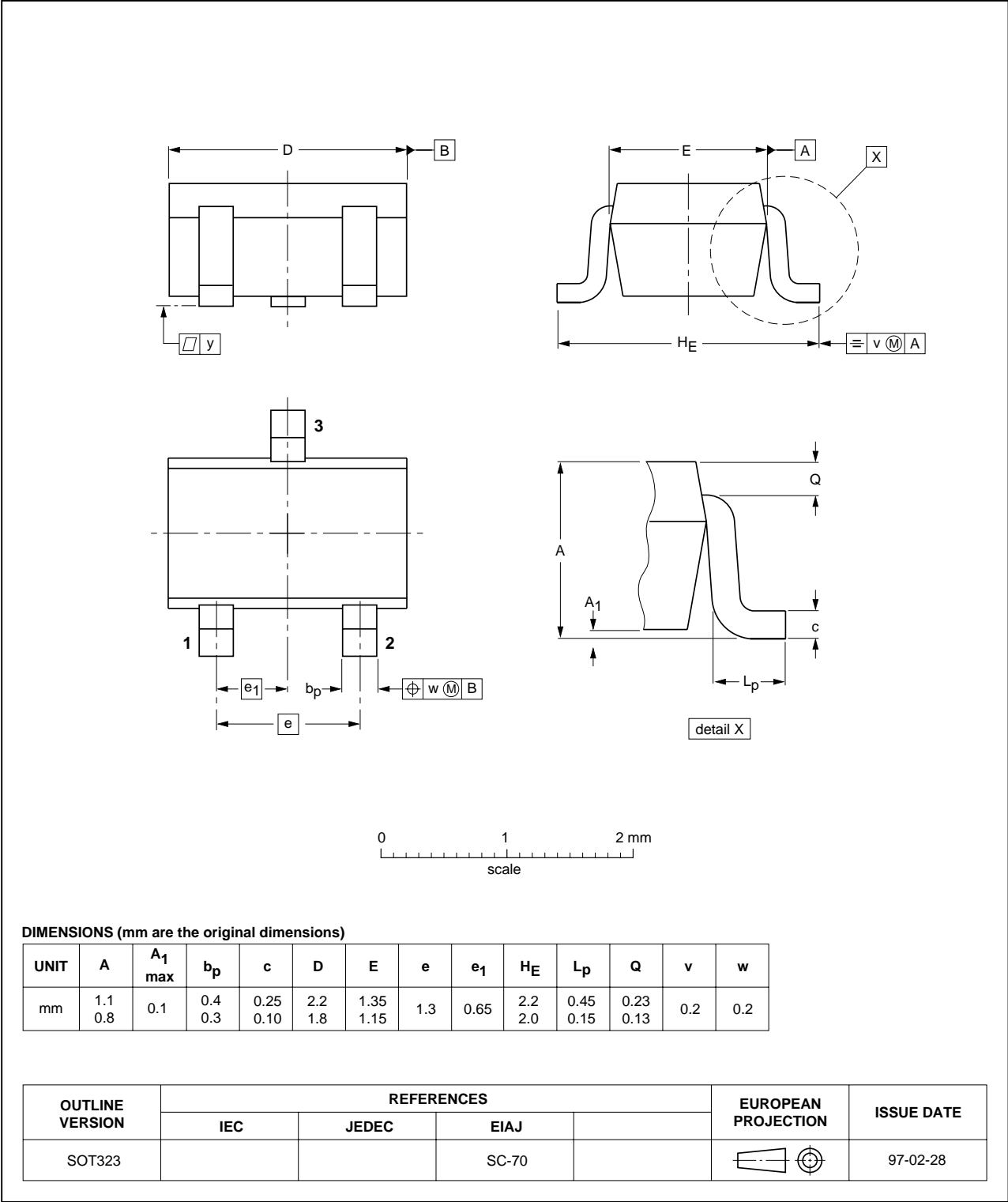
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	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28 99-09-13

PNP resistor-equipped transistors;
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Plastic surface mounted package; 3 leads

SOT323



PNP resistor-equipped transistors;
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Printed in The Netherlands

R75/07/pp14

Date of release: 2004 Aug 05

Document order number: 9397 750 13659

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